

October 2008

FDY6342L

Integrated Load Switch

Features

- Max $r_{DS(on)} = 0.5 \Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_D = -0.83 \text{ A}$
- Max $r_{DS(on)} = 0.7 \Omega$ at $V_{GS} = 2.5 \text{ V}$, $I_D = -0.70 \text{ A}$
- Max $r_{DS(on)} = 1.2 \Omega$ at $V_{GS} = 1.8 \text{ V}$, $I_D = -0.43 \text{ A}$
- Max $r_{DS(on)} = 1.8 \Omega$ at $V_{GS} = 1.5 \text{ V}$, $I_D = -0.36 \text{ A}$
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>4 kV Human body model)
- High performance trench technology for extremely low r_{DS(on)}
- Compact industry standard SC89-6 surface mount package
- RoHS Compliant

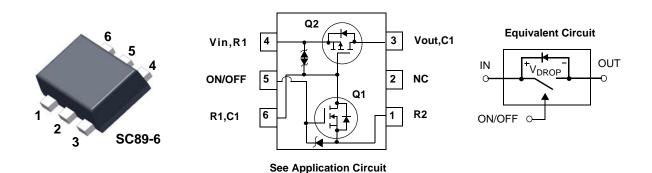


General Description

This device is particularly suited for compact power management in portable electronic equipment where 2.5 V to 8 V input and 0.83 A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large P-Channel power MOSFET (Q2) in one tiny SC89-6 package.

Applications

- Power management
- Load switch



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units		
V _{IN}	Gate to Source Voltage (Q2)		±8	V	
V _{ON/OFF}	Gate to Source Voltage (Q1)		-0.5 to 8	V	
I _{Load}	Load Current -Continuous	(Note 2)	-0.83	A	
	-Pulsed	(Note 2)	-1.0		
Б	Power Dissipation	(Note 1a)	0.625	10/	
P_{D}	Power Dissipation	(Note 1b)	0.446	W	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C	

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	200	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	280	C/VV

Package Marking and Ordering Information

Device Marking Device		Package Reel Size		Tape Width	Quantity	
Н	FDY6342L	SC89-6	7 "	8 mm	3000 units	

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Parameter

Off Characteristics							
BV_{IN}	V _{IN} Breakdown Voltage	$I_D = -250 \mu A, V_{ON/OFF} = 0 V$	8			V	
I _{Load}	Zero Gate Voltage Drain Current	$V_{IN} = -6.4 \text{ V}, V_{ON/OFF} = 0 \text{ V}$			-1	μΑ	
I _{FL}	Leakage Current, Forward	V _{IN} = 8 V, V _{ON/OFF} = 0 V			10	μΑ	
I _{RL}	Leakage Current, Reverse	$V_{IN} = -8 \text{ V}, V_{ON/OFF} = 0 \text{ V}$			-10	μΑ	

Test Conditions

On Characteristics (note 2)

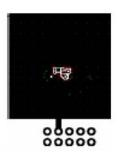
Symbol

V _{ON/OFF(th)}	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}$, $I_D = -250 \mu A$	0.65	0.85	1.5	V
	Static Drain to Source On Resistance (Q2)	$V_{IN} = 4.5 \text{ V}, I_{D} = -0.83 \text{ A}$		0.28	0.5	Ω
		$V_{IN} = 2.5 \text{ V}, I_D = -0.70 \text{ A}$		0.35	0.7	
r _{DS(on)}		$V_{IN} = 1.8 \text{ V}, I_D = -0.43 \text{ A}$		0.45	1.2	
-(-,		$V_{IN} = 1.5 \text{ V}, I_D = -0.36 \text{ A}$		0.57	1.8	
		$V_{IN} = 4.5 \text{ V}, I_D = 0.4 \text{ A}$		2.9	4.0	Ω
		$V_{IN} = 2.7 \text{ V}, I_D = 0.2 \text{ A}$		3.5	5.0	52

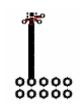
Drain-Source Diode Characteristics

Ī	l _S	Maximum Continuous Drain to Source Diode Forward Current			-0.25	V
,	V_{SD}	Source to Drain Diode Forward Voltage	$V_{ON/OFF} = 0 \text{ V}, I_S = -0.25 \text{ A (Note 2)}$	-0.8	-1.2	V

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a)200 °C/W when mounted on a 1 in² pad of 2 oz copper.



b)280 °C/W when mounted on a minimum pad of 2 oz copper.

Min

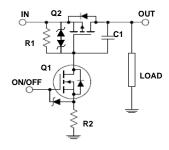
Тур

Max

Units

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.

FDY6342L Load Switch Application circuit



External Component Recommendation:

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030

Typical Characteristics T_J = 25 °C unless otherwise noted

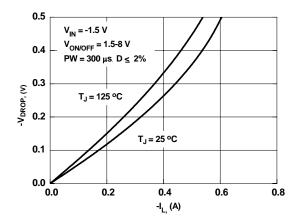


Figure 1. Conduction Voltage Drop Variation with Load Current

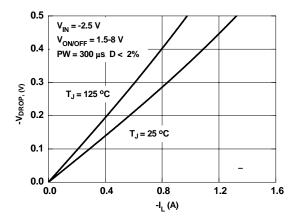


Figure 3. Conduction Voltage Drop Variation with Load Current

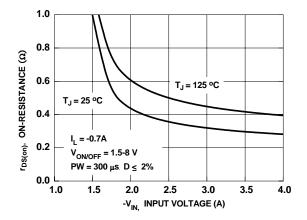


Figure 5. On-Resistance Variaton with Input Current

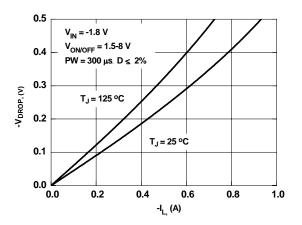


Figure 2. Conduction Voltage Drop Variation with Load Current

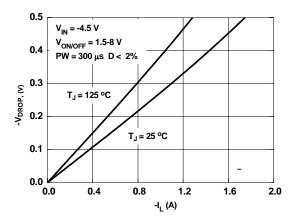


Figure 4. Conduction Voltage Drop Variation with Load Current

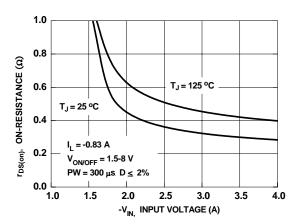
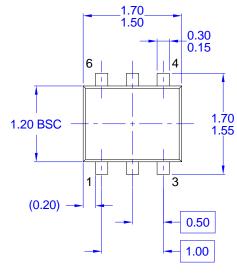
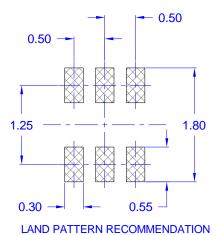
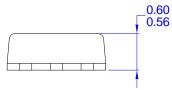


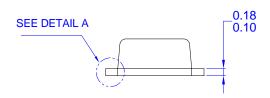
Figure 6. On-Resistance Variaton with Input Current

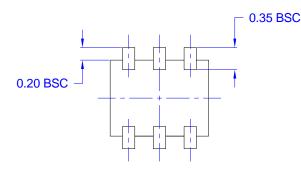
Dimensional Outline and Pad Layout

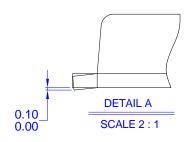












NOTES: UNLESS OTHERWISE SPECIFIED A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.

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